

L Number	Hits	Search Text	DB	Time stamp
-	9844	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$4)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:15
-	10015	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$45)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 07:54
-	7329	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$45)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 07:57
-	10011	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$5)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 07:57
-	733	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$5)).clm.) and capacit\$5.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 07:57
-	264	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$5)).clm.) and capacit\$5.clm.) and electrode.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/01 07:57
-	53	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$5)).clm.) and capacit\$5.clm.) and electrode.clm.) and (concentration impurity purity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:36
-	17	((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 (conduct\$5)).clm.) and capacit\$5.clm.) and electrode.clm.) and (concentration impurity purity).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:28
-	700	(216/2).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:36
-	92	((216/2).CCLS.) and impurit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:37
-	1	((216/2).CCLS.) and impurit\$4 near3 concentration) and etch near1 pit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:39
-	1	((216/2).CCLS.) and impurit\$4 near3 concentration) and etch near1 pit) and diaphragm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:39
-	23	((216/2).CCLS.) and impurit\$4 near3 concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:41
-	20	((216/2).CCLS.) and impurit\$4 near3 concentration) and etch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:48

-	15	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:32
-	3	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)) and etch near3 (pit hole groove dip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:26
-	3	((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch near3 (pit hole groove dip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:49
-	2	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)) and electrode near3 dielectric near3 (film layer support substrate cover\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:57
-	1	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)) and electrode near3 dielectric near3 (film layer support substrate cover\$4)) and pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:55
-	1	((((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)) and electrode near3 dielectric near3 (film layer support substrate cover\$4)) and pressure) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 18:55
-	11	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)) and pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:04
-	6	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)) and pressure near3 (sens\$4 measur\$3 detect test transducer gauge monitor evaluate estimat\$4 identif\$4 indicat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:27
-	44167	impurit\$4 near3 concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:27
-	1092	(impurit\$4 near3 concentration) and pressure near3 (sens\$4 measur\$3 detect test transducer gauge monitor evaluate estimat\$4 identif\$4 indicat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:29
-	18	((impurit\$4 near3 concentration) and pressure near3 (sens\$4 measur\$3 detect test transducer gauge monitor evaluate estimat\$4 identif\$4 indicat\$4)) and etch near3 (pit groove hole dip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:30
-	13	((impurit\$4 near3 concentration) and pressure near3 (sens\$4 measur\$3 detect test transducer gauge monitor evaluate estimat\$4 identif\$4 indicat\$4)) and etch near3 (pit groove hole dip)) and (diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/26 19:32

-	29	(diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 conduct\$4 same etch\$4 same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:51
-	3	(diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 conduct\$4 same etch\$4 same pit same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:23
-	658	(361/283.1-283.4).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:24
-	1	((361/283.1-283.4).CCLS.) and etch\$4 same pit same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:35
-	0	((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:36
-	0	((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:38
-	919	((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:48
-	2	((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:48
-	2	((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:47
-	2	((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:48
-	0	((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) near4 density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:47
-	1694	((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:48
-	4	((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:48
-	4	((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:49

-	261	(diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 conduct\$4 same etch\$4 same (pit\$4 hole\$4 groove\$4 recess\$4 opening\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:52
-	8	((((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and ((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 conduct\$4 same etch\$4 same (pit\$4 hole\$4 groove\$4 recess\$4 opening\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:52
-	12	(diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2 conduct\$4 same etch\$4 same (pit\$4 hole\$4 groove\$4 recess\$4 opening\$4) same density	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:53